

深圳市晶泰源电子有限公司

KSA1175 TRANSISTOR (PNP)

FEATURES

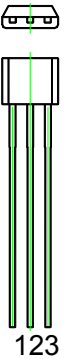
- Collector-Base Voltage : $V_{CBO} = -60V$
- Complement to KSC2785

MAXIMUM RATINGS ($T_A = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current (DC)	-0.15	A
P_C	Collector Power Dissipation	0.25	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55-150	$^\circ C$

TO-92S

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1mA, I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -6V, I_C = -1mA$	40		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$			-0.3	V
Base-emitter voltage	V_{BE}	$V_{CE} = -6V, I_C = -1mA$	-0.5		-0.8	V
Transition frequency	f_T	$V_{CE} = -6V, I_C = -10mA$	50			MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		2.8		pF
Noise figure	NF	$V_{CE} = -6V, I_C = -0.3mA, f = 100Hz, R_g = 10K\Omega$			20	dB

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	G	L
Range	40-80	70-140	120-240	200-400	350-700
Marking					